

300mA HIGH SPEED, EXTREMELY LOW NOISE CMOS LDO REGULATOR AP2125

General Description

The AP2125 series are 300mA, positive voltage regulator ICs fabricated by CMOS process.

Each of these ICs is equipped with a voltage reference, an error amplifier, a resistor network for setting output voltage, a chip enable circuit, a current limit circuit and OTSD (over temperature shut down) circuit to prevent the IC from over current and over temperature.

The AP2125 series have features of high ripple rejection, low dropout voltage, low noise, high output voltage accuracy and low current consumption which make them ideal for use in various battery-powered apparatus.

The AP2125 have 1.8V, 2.5V, 2.8V, 3.0V, 3.3V and 4.2V fixed voltage versions.

These ICs are available in tiny SC-70-5 and SC-82 packages as well as industry standard SOT-23-3 and SOT-23-5 packages.

Features

- Excellent Ripple Rejection: 70dB Typical (1.8V Version)
- Low Dropout Voltage: 65mV ($I_{OUT}=100mA$, 3.3V Version)
- Low Standby Current: 0.01 μA Typical
- Low Quiescent Current: 60 μA Typical
- Extremely Low Noise: 50 μV_{rms} Typical
- Maximum Output Current: 300mA (Min.)
- High Output Voltage Accuracy: $\pm 2\%$
- Compatible with Low ESR Ceramic Capacitor
- Excellent Line/Load Regulation

Applications

- CDMA/GSM Cellular Handsets
- Battery-powered Equipments
- Laptops, Palmtops, Notebook Computers
- Hand-held Instruments
- PCMCIA Cards
- Portable Information Appliances

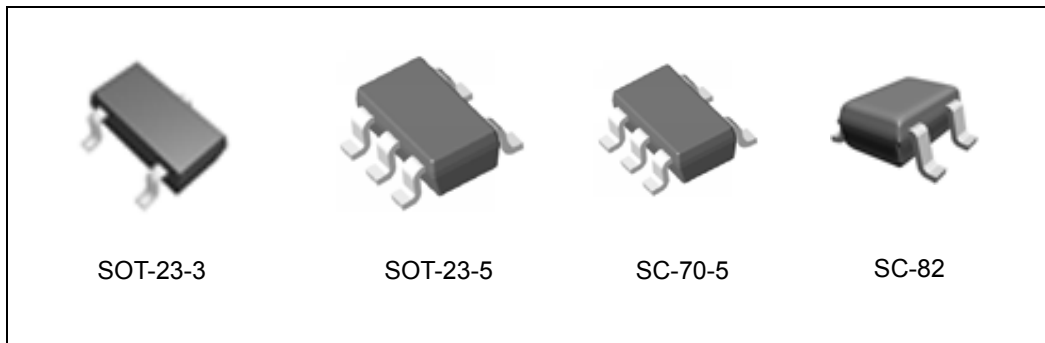


Figure 1. Package Types of AP2125

Pin Configuration

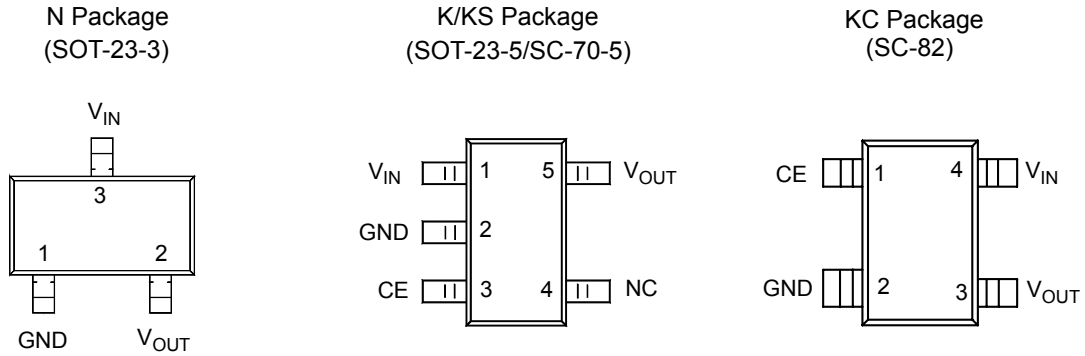
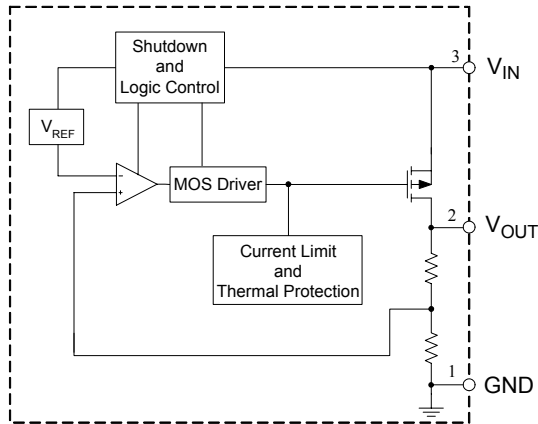


Figure 2. Pin Configuration of AP2125 (Top View)

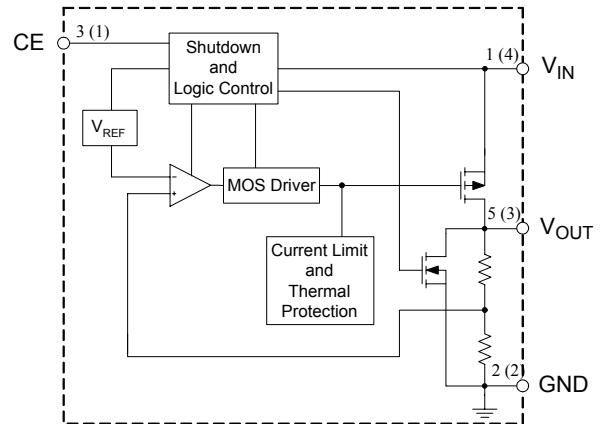
Pin Description

Pin Number			Pin Name	Function
SOT-23-3	SOT-23-5/ SC-70-5	SC-82		
3	1	4	V_{IN}	Input voltage
1	2	2	GND	Ground
	3	1	CE	Active high enable input pin. Logic high=enable, logic low=shutdown
	4		NC	No connection
2	5	3	V_{OUT}	Regulated output voltage

Functional Block Diagram



SOT-23-3



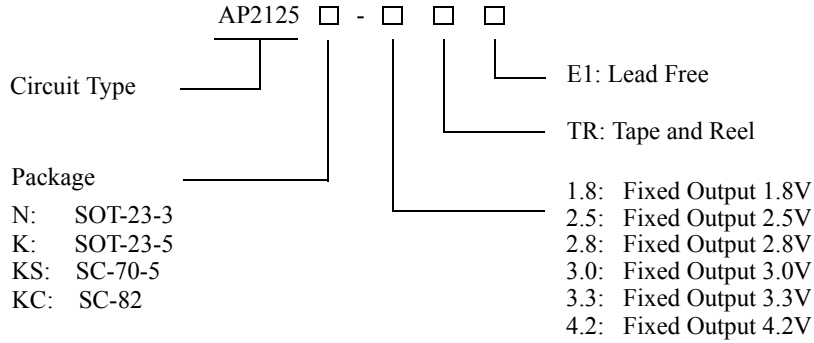
A(B)
 A SOT-23-5/SC-70-5
 B SC-82

Figure 3. Functional Block Diagram of AP2125



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Ordering Information



Package	Temperature Range	Part Number	Marking ID	Packing Type
SOT-23-3	-40 to 85°C	AP2125N-1.8TRE1	EJ2	Tape & Reel
		AP2125N-2.5TRE1	EJ4	Tape & Reel
		AP2125N-2.8TRE1	EJ5	Tape & Reel
		AP2125N-3.0TRE1	EJ6	Tape & Reel
		AP2125N-3.3TRE1	EJ7	Tape & Reel
		AP2125N-4.2TRE1	EJ3	Tape & Reel
SOT-23-5	-40 to 85°C	AP2125K-1.8TRE1	ECB	Tape & Reel
		AP2125K-2.5TRE1	ECD	Tape & Reel
		AP2125K-2.8TRE1	ECE	Tape & Reel
		AP2125K-3.0TRE1	ECF	Tape & Reel
		AP2125K-3.3TRE1	ECG	Tape & Reel
		AP2125K-4.2TRE1	ECC	Tape & Reel
SC-70-5	-40 to 85°C	AP2125KS-1.8TRE1	26	Tape & Reel
		AP2125KS-2.5TRE1	35	Tape & Reel
		AP2125KS-2.8TRE1	27	Tape & Reel
		AP2125KS-3.0TRE1	36	Tape & Reel
		AP2125KS-3.3TRE1	28	Tape & Reel
		AP2125KS-4.2TRE1	34	Tape & Reel
SC-82	-40 to 85°C	AP2125KC-1.8TRE1	91	Tape & Reel
		AP2125KC-2.5TRE1	96	Tape & Reel
		AP2125KC-2.8TRE1	92	Tape & Reel
		AP2125KC-3.0TRE1	97	Tape & Reel
		AP2125KC-3.3TRE1	93	Tape & Reel
		AP2125KC-4.2TRE1	95	Tape & Reel

BCD Semiconductor's Pb-free products, as designated with "E1" suffix in the part number, are RoHS compliant.

**300mA HIGH SPEED, EXTREMELY LOW NOISE CMOS LDO REGULATOR AP2125****Absolute Maximum Ratings (Note 1)**

Parameter	Symbol	Value	Unit	
Input Voltage	V_{IN}	6.5	V	
Enable Input Voltage	V_{CE}	-0.3 to $V_{IN}+0.3$	V	
Output Current	I_{OUT}	450	mA	
Junction Temperature	T_J	150	°C	
Storage Temperature Range	T_{STG}	-65 to 150	°C	
Lead Temperature (Soldering, 10sec)	T_{LEAD}	260	°C	
Thermal Resistance	θ_{JA}	SOT-23-3	200	°C/W
		SOT-23-5	200	
		SC-70-5	300	
		SC-82	300	
ESD (Human Body Model)	ESD	6000	V	
ESD (Machine Model)	ESD	400	V	

Note 1: Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "Recommended Operating Conditions" is not implied. Exposure to "Absolute Maximum Ratings" for extended periods may affect device reliability.

Recommended Operating Conditions

Parameter	Symbol	Min	Max	Unit
Input Voltage	V_{IN}	$V_{OUT}+0.5V$	6	V
Operating Ambient Temperature Range	T_A	-40	85	°C



300mA HIGH SPEED, EXTREMELY LOW NOISE CMOS LDO REGULATOR AP2125

Electrical Characteristics
AP2125-1.8 Electrical Characteristics

($V_{IN}=2.8V$, $T_A=25^{\circ}C$, $C_{IN}=1\mu F$, $C_{OUT}=1\mu F$, **Bold** typeface applies over $-40^{\circ}C \leq T_J \leq 85^{\circ}C$, unless otherwise specified.)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit	
Output Voltage	V_{OUT}	$V_{IN}=2.8V$ $1mA \leq I_{OUT} \leq 30mA$	1.764	1.8	1.836	V	
Input Voltage	V_{IN}				6	V	
Maximum Output Current	$I_{OUT(MAX)}$	$V_{IN}-V_{OUT}=1V$, $V_{OUT}=1.76V$	300	360		mA	
Load Regulation	V_{RLOAD}	$V_{IN}=2.8V$ $1mA \leq I_{OUT} \leq 300mA$		6		mV	
Line Regulation	V_{RLINE}	$2.8V \leq V_{IN} \leq 6V$ $I_{OUT}=30mA$		1		mV	
Dropout Voltage	V_{DROP}	$I_{OUT}=10mA$		10	12	mV	
		$I_{OUT}=100mA$		100	120		
		$I_{OUT}=300mA$		300	360		
Quiescent Current	I_Q	$V_{IN}=2.8V$, $I_{OUT}=0mA$		60	90	μA	
Standby Current	I_{STD}	$V_{IN}=2.8V$ V_{CE} in OFF mode		0.01	1.0	μA	
Power Supply Rejection Ratio	PSRR	Ripple 0.5Vp-p $V_{IN}=2.8V$	$f=100Hz$		70		dB
			$f=1KHz$		70		dB
Output Voltage Temperature Coefficient	$(\Delta V_{OUT}/V_{OUT})/\Delta T$	$I_{OUT}=30mA$		± 100		ppm/ $^{\circ}C$	
Short Current Limit	I_{SHORT}	$V_{OUT}=0V$		50		mA	
RMS Output Noise	V_{NOISE}	$10Hz \leq f \leq 100kHz$		50		μV_{rms}	
CE "High" Voltage		CE input voltage "High"	1.5			V	
CE "Low" Voltage		CE input voltage "Low"			0.4	V	
Thermal Shutdown				160		$^{\circ}C$	
Thermal Shutdown Hysteresis				25		$^{\circ}C$	



300mA HIGH SPEED, EXTREMELY LOW NOISE CMOS LDO REGULATOR AP2125

Electrical Characteristics (Continued)

AP2125-2.5 Electrical Characteristics

($V_{IN}=3.5V$, $T_A=25^{\circ}C$, $C_{IN}=1\mu F$, $C_{OUT}=1\mu F$, **Bold** typeface applies over $-40^{\circ}C \leq T_J \leq 85^{\circ}C$, unless otherwise specified.)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit	
Output Voltage	V_{OUT}	$V_{IN}=3.5V$ $1mA \leq I_{OUT} \leq 30mA$	2.45	2.5	2.55	V	
Input Voltage	V_{IN}				6	V	
Maximum Output Current	$I_{OUT(MAX)}$	$V_{IN}-V_{OUT}=1V$, $V_{OUT}=2.45V$	300	360		mA	
Load Regulation	V_{RLOAD}	$V_{IN}=3.5V$ $1mA \leq I_{OUT} \leq 300mA$		10		mV	
Line Regulation	V_{RLINE}	$3.5V \leq V_{IN} \leq 6V$ $I_{OUT}=30mA$		1		mV	
Dropout Voltage	V_{DROP}	$I_{OUT}=10mA$		6.5	10	mV	
		$I_{OUT}=100mA$		65	100		
		$I_{OUT}=300mA$		200	300		
Quiescent Current	I_Q	$V_{IN}=3.5V$, $I_{OUT}=0mA$		60	90	μA	
Standby Current	I_{STD}	$V_{IN}=3.5V$ V_{CE} in OFF mode		0.01	1.0	μA	
Power Supply Rejection Ratio	PSRR	Ripple 0.5Vp-p $V_{IN}=3.5V$	$f=100Hz$		65		dB
			$f=1KHz$		65		dB
Output Voltage Temperature Coefficient	$(\Delta V_{OUT}/V_{OUT})/\Delta T$	$I_{OUT}=30mA$		± 100		ppm/ $^{\circ}C$	
Short Current Limit	I_{SHORT}	$V_{OUT}=0V$		50		mA	
RMS Output Noise	V_{NOISE}	$10Hz \leq f \leq 100kHz$		50		μV_{rms}	
CE "High" Voltage		CE input voltage "High"	1.5			V	
CE "Low" Voltage		CE input voltage "Low"			0.4	V	
Thermal Shutdown				160		$^{\circ}C$	
Thermal Shutdown Hysteresis				25		$^{\circ}C$	



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Electrical Characteristics (Continued)

AP2125-2.8 Electrical Characteristics

($V_{IN}=3.8V$, $T_A=25^{\circ}C$, $C_{IN}=1\mu F$, $C_{OUT}=1\mu F$, **Bold** typeface applies over $-40^{\circ}C \leq T_J \leq 85^{\circ}C$, unless otherwise specified.)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit	
Output Voltage	V_{OUT}	$V_{IN}=3.8V$ $1mA \leq I_{OUT} \leq 30mA$	2.744	2.8	2.856	V	
Input Voltage	V_{IN}				6	V	
Maximum Output Current	$I_{OUT(MAX)}$	$V_{IN}-V_{OUT}=1V$, $V_{OUT}=2.74V$	300	360		mA	
Load Regulation	V_{RLOAD}	$V_{IN}=3.8V$ $1mA \leq I_{OUT} \leq 300mA$		11		mV	
Line Regulation	V_{RLINE}	$3.8V \leq V_{IN} \leq 6V$ $I_{OUT}=30mA$		1		mV	
Dropout Voltage	V_{DROP}	$I_{OUT}=10mA$		6.5	10	mV	
		$I_{OUT}=100mA$		65	100		
		$I_{OUT}=300mA$		200	300		
Quiescent Current	I_Q	$V_{IN}=3.8V$, $I_{OUT}=0mA$		60	90	μA	
Standby Current	I_{STD}	$V_{IN}=3.8V$ V_{CE} in OFF mode		0.01	1.0	μA	
Power Supply Rejection Ratio	PSRR	Ripple 0.5Vp-p $V_{IN}=3.8V$	$f=100Hz$		65		dB
			$f=1KHz$		65		dB
Output Voltage Temperature Coefficient	$(\Delta V_{OUT}/V_{OUT})/\Delta T$	$I_{OUT}=30mA$		± 100		ppm/ $^{\circ}C$	
Short Current Limit	I_{SHORT}	$V_{OUT}=0V$		50		mA	
RMS Output Noise	V_{NOISE}	$10Hz \leq f \leq 100kHz$		50		μV_{rms}	
CE "High" Voltage		CE input voltage "High"	1.5			V	
CE "Low" Voltage		CE input voltage "Low"			0.4	V	
Thermal Shutdown				160		$^{\circ}C$	
Thermal Shutdown Hysteresis				25		$^{\circ}C$	



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Electrical Characteristics (Continued)

AP2125-3.0 Electrical Characteristics

($V_{IN}=4.0V$, $T_A=25^{\circ}C$, $C_{IN}=1\mu F$, $C_{OUT}=1\mu F$, **Bold** typeface applies over $-40^{\circ}C \leq T_J \leq 85^{\circ}C$, unless otherwise specified.)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit	
Output Voltage	V_{OUT}	$V_{IN}=4.0V$ $1mA \leq I_{OUT} \leq 30mA$	2.94	3.0	3.06	V	
Input Voltage	V_{IN}				6	V	
Maximum Output Current	$I_{OUT(MAX)}$	$V_{IN}-V_{OUT}=1V$, $V_{OUT}=2.94V$	300	360		mA	
Load Regulation	V_{RLOAD}	$V_{IN}=4.0V$ $1mA \leq I_{OUT} \leq 300mA$		12		mV	
Line Regulation	V_{RLINE}	$4.0V \leq V_{IN} \leq 6V$ $I_{OUT}=30mA$		1		mV	
Dropout Voltage	V_{DROP}	$I_{OUT}=10mA$		6.5	10	mV	
		$I_{OUT}=100mA$		65	100		
		$I_{OUT}=300mA$		200	300		
Quiescent Current	I_Q	$V_{IN}=4.0V$, $I_{OUT}=0mA$		60	90	μA	
Standby Current	I_{STD}	$V_{IN}=4.0V$ V_{CE} in OFF mode		0.01	1.0	μA	
Power Supply Rejection Ratio	PSRR	Ripple 0.5Vp-p $V_{IN}=4.0V$	$f=100Hz$		65		dB
			$f=1KHz$		65		dB
Output Voltage Temperature Coefficient	$(\Delta V_{OUT}/V_{OUT})/\Delta T$	$I_{OUT}=30mA$		± 100		ppm/ $^{\circ}C$	
Short Current Limit	I_{SHORT}	$V_{OUT}=0V$		50		mA	
RMS Output Noise	V_{NOISE}	$10Hz \leq f \leq 100kHz$		50		μV_{rms}	
CE "High" Voltage		CE input voltage "High"	1.5			V	
CE "Low" Voltage		CE input voltage "Low"			0.4	V	
Thermal Shutdown				160		$^{\circ}C$	
Thermal Shutdown Hysteresis				25		$^{\circ}C$	



300mA HIGH SPEED, EXTREMELY LOW NOISE CMOS LDO REGULATOR AP2125

Electrical Characteristics (Continued)

AP2125-3.3 Electrical Characteristics

($V_{IN}=4.3V$, $T_A=25^{\circ}C$, $C_{IN}=1\mu F$, $C_{OUT}=1\mu F$, **Bold** typeface applies over $-40^{\circ}C \leq T_J \leq 85^{\circ}C$, unless otherwise specified.)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit	
Output Voltage	V_{OUT}	$V_{IN}=4.3V$ $1mA \leq I_{OUT} \leq 30mA$	3.234	3.3	3.366	V	
Input Voltage	V_{IN}				6	V	
Maximum Output Current	$I_{OUT(MAX)}$	$V_{IN}-V_{OUT}=1V$, $V_{OUT}=3.23V$	300	360		mA	
Load Regulation	V_{RLOAD}	$V_{IN}=4.3V$ $1mA \leq I_{OUT} \leq 300mA$		13		mV	
Line Regulation	V_{RLINE}	$4.3V \leq V_{IN} \leq 6V$ $I_{OUT}=30mA$		1		mV	
Dropout Voltage	V_{DROP}	$I_{OUT}=10mA$		6.5	10	mV	
		$I_{OUT}=100mA$		65	100		
		$I_{OUT}=300mA$		200	300		
Quiescent Current	I_Q	$V_{IN}=4.3V$, $I_{OUT}=0mA$		60	90	μA	
Standby Current	I_{STD}	$V_{IN}=4.3V$ V_{CE} in OFF mode		0.01	1.0	μA	
Power Supply Rejection Ratio	PSRR	Ripple 0.5Vp-p $V_{IN}=4.3V$	$f=100Hz$		65		dB
			$f=1KHz$		65		dB
Output Voltage Temperature Coefficient	$(\Delta V_{OUT}/V_{OUT})/\Delta T$	$I_{OUT}=30mA$		± 100		ppm/ $^{\circ}C$	
Short Current Limit	I_{SHORT}	$V_{OUT}=0V$		50		mA	
RMS Output Noise	V_{NOISE}	$10Hz \leq f \leq 100kHz$		50		μV_{rms}	
CE "High" Voltage		CE input voltage "High"	1.5			V	
CE "Low" Voltage		CE input voltage "Low"			0.4	V	
Thermal Shutdown				160		$^{\circ}C$	
Thermal Shutdown Hysteresis				25		$^{\circ}C$	



300mA HIGH SPEED, EXTREMELY LOW NOISE CMOS LDO REGULATOR AP2125

Electrical Characteristics (Continued)

AP2125-4.2 Electrical Characteristics

($V_{IN}=5.2V$, $T_A=25^{\circ}C$, $C_{IN}=1\mu F$, $C_{OUT}=1\mu F$, **Bold** typeface applies over $-40^{\circ}C \leq T_J \leq 85^{\circ}C$, unless otherwise specified.)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit	
Output Voltage	V_{OUT}	$V_{IN}=5.2V$ $1mA \leq I_{OUT} \leq 30mA$	4.116	4.2	4.284	V	
Input Voltage	V_{IN}				6	V	
Maximum Output Current	$I_{OUT(MAX)}$	$V_{IN}-V_{OUT}=1V$, $V_{OUT}=4.12V$	300	360		mA	
Load Regulation	V_{RLOAD}	$V_{IN}=5.2V$ $1mA \leq I_{OUT} \leq 300mA$		13		mV	
Line Regulation	V_{RLINE}	$5.2V \leq V_{IN} \leq 6V$ $I_{OUT}=30mA$		1		mV	
Dropout Voltage	V_{DROP}	$I_{OUT}=10mA$		6.5	10	mV	
		$I_{OUT}=100mA$		65	100		
		$I_{OUT}=300mA$		200	300		
Quiescent Current	I_Q	$V_{IN}=5.2V$, $I_{OUT}=0mA$		60	90	μA	
Standby Current	I_{STD}	$V_{IN}=5.2V$ V_{CE} in OFF mode		0.01	1.0	μA	
Power Supply Rejection Ratio	PSRR	Ripple 0.5Vp-p $V_{IN}=5.2V$	$f=100Hz$		65		dB
			$f=1KHz$		65		dB
Output Voltage Temperature Coefficient	$(\Delta V_{OUT}/V_{OUT})/\Delta T$	$I_{OUT}=30mA$		± 100		ppm/ $^{\circ}C$	
Short Current Limit	I_{SHORT}	$V_{OUT}=0V$		50		mA	
RMS Output Noise	V_{NOISE}	$10Hz \leq f \leq 100kHz$		50		μV_{rms}	
CE "High" Voltage		CE input voltage "High"	1.5			V	
CE "Low" Voltage		CE input voltage "Low"			0.4	V	
Thermal Shutdown				160		$^{\circ}C$	
Thermal Shutdown Hysteresis				25		$^{\circ}C$	



300mA HIGH SPEED, EXTREMELY LOW NOISE CMOS LDO REGULATOR AP2125

Typical Performance Characteristics

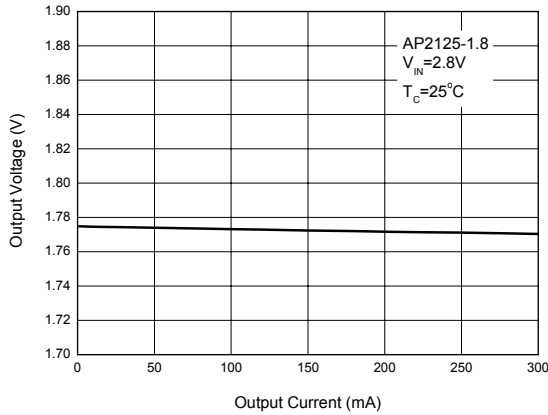


Figure 4. Output Voltage vs. Output Current

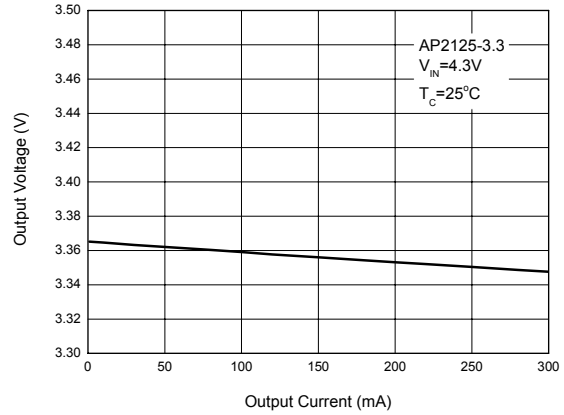


Figure 5. Output Voltage vs. Output Current

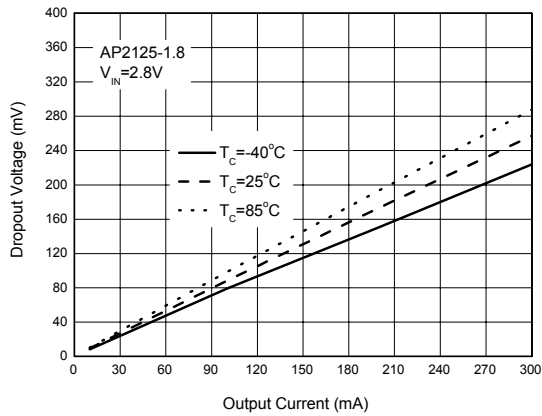


Figure 6. Dropout Voltage vs. Output Current

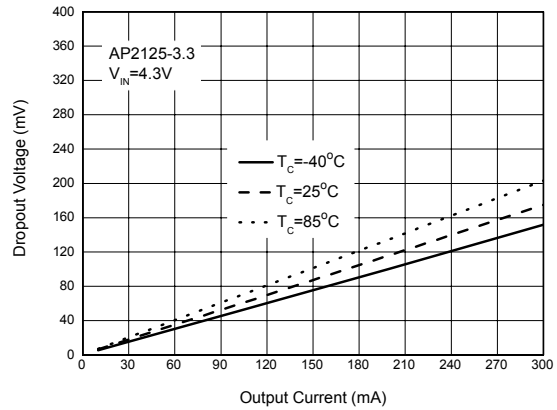


Figure 7. Dropout Voltage vs. Output Current



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Typical Performance Characteristics (Continued)

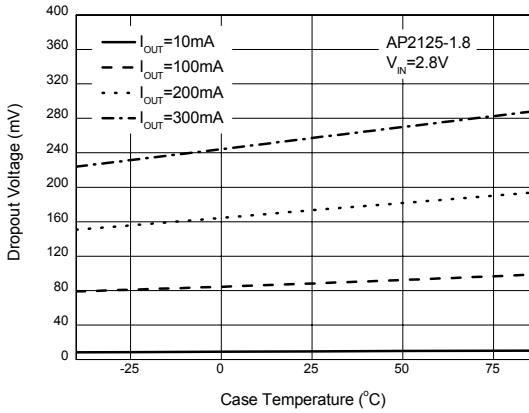


Figure 8. Dropout Voltage vs. Case Temperature

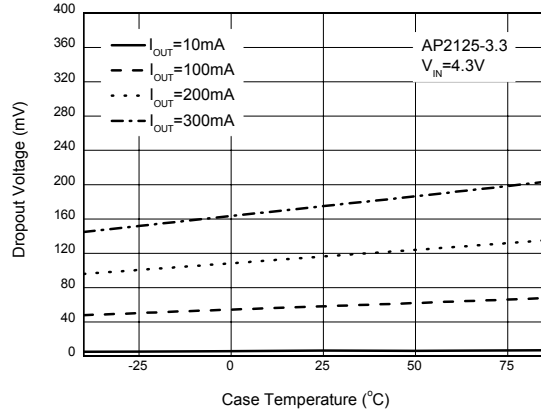


Figure 9. Dropout Voltage vs. Case Temperature

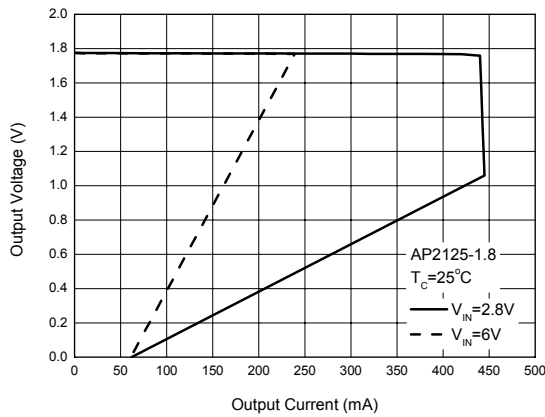


Figure 10. Current Limit

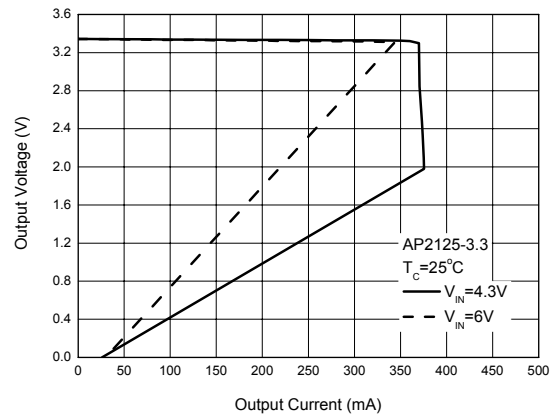


Figure 11. Current Limit



300mA HIGH SPEED, EXTREMELY LOW NOISE CMOS LDO REGULATOR AP2125

Typical Performance Characteristics (Continued)

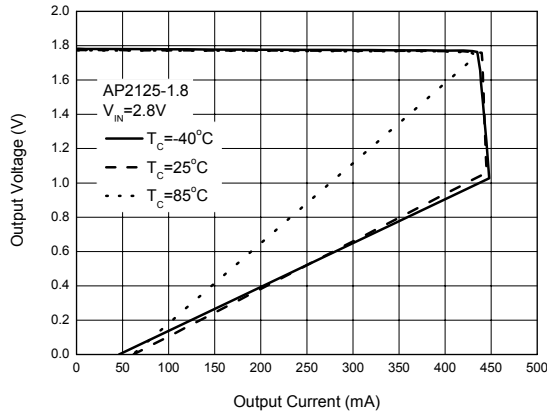


Figure 12. Current Limit

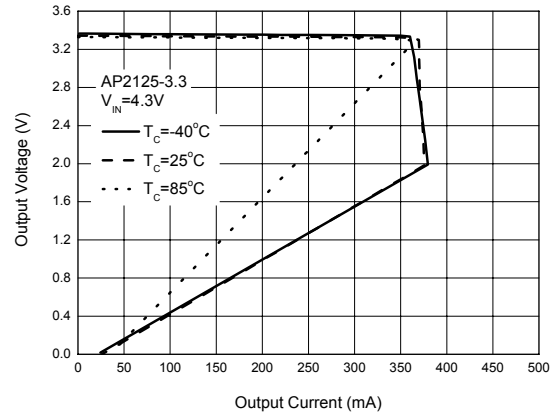


Figure 13. Current Limit

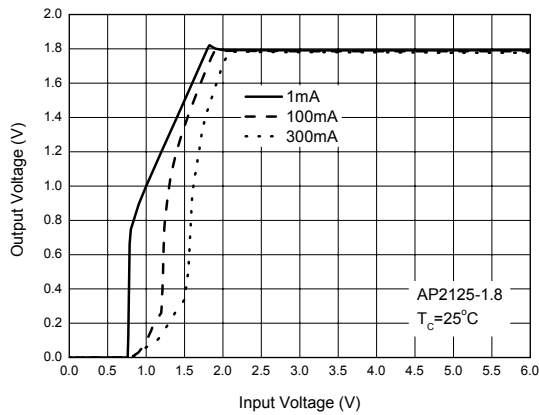


Figure 14. Output Voltage vs. Input Voltage

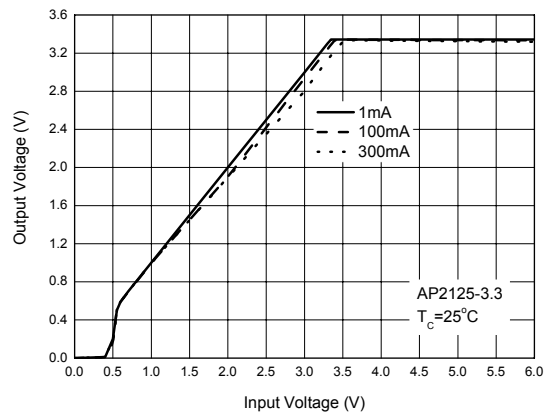


Figure 15. Output Voltage vs. Input Voltage



300mA HIGH SPEED, EXTREMELY LOW NOISE CMOS LDO REGULATOR AP2125

Typical Performance Characteristics (Continued)

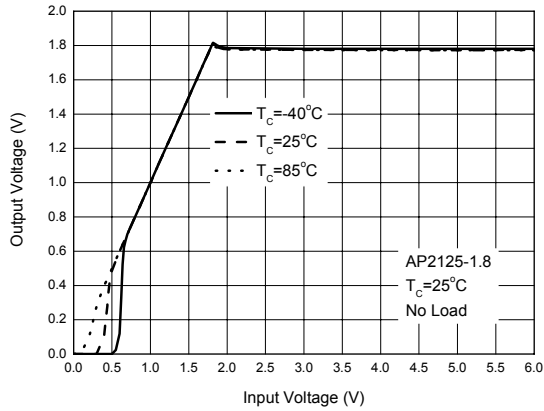


Figure 16. Output Voltage vs. Input Voltage

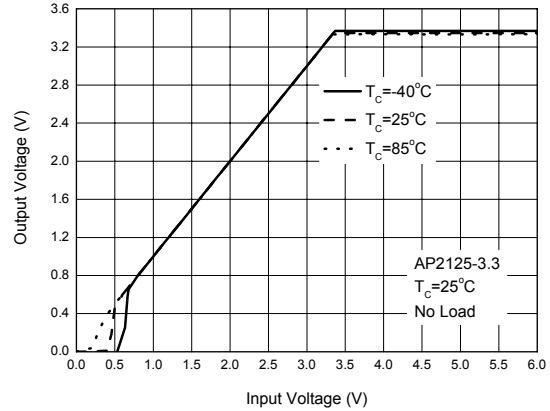


Figure 17. Output Voltage vs. Input Voltage

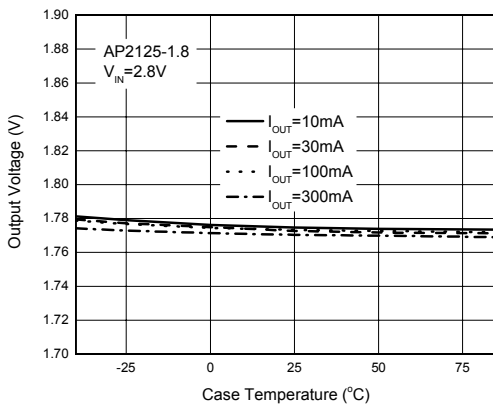


Figure 18. Output Voltage vs. Case Temperature

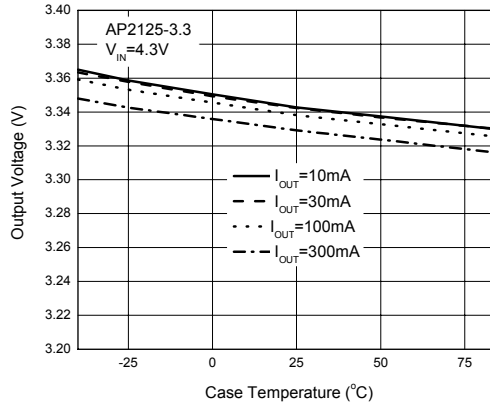


Figure 19. Output Voltage vs. Case Temperature

300mA HIGH SPEED, EXTREMELY LOW NOISE CMOS LDO REGULATOR AP2125

Typical Performance Characteristics (Continued)

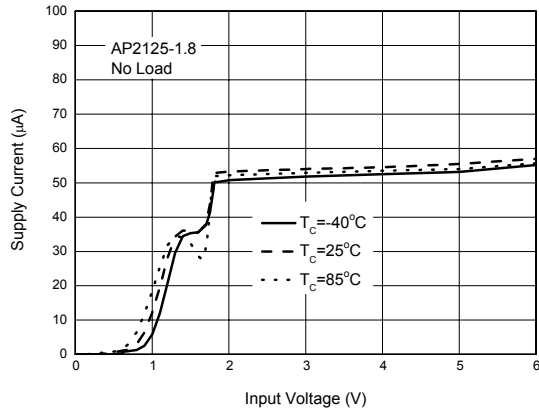


Figure 20. Supply Current vs. Input Voltage

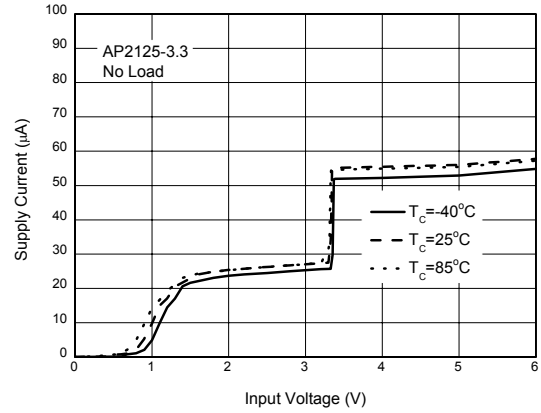


Figure 21. Supply Current vs. Input Voltage

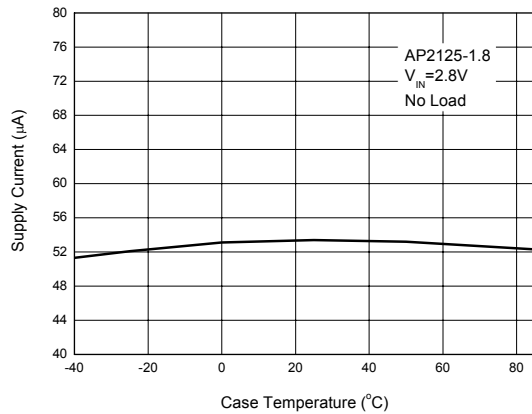


Figure 22. Supply Current vs. Case Temperature

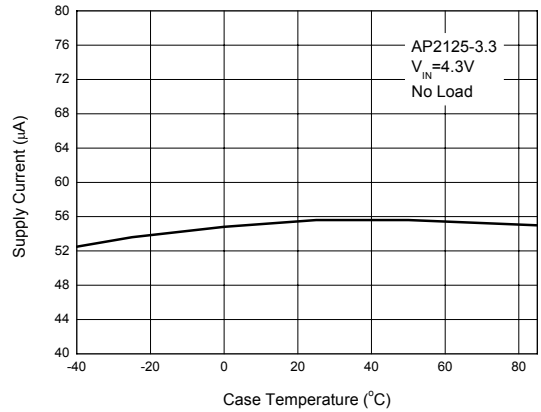


Figure 23. Supply Current vs. Case Temperature

300mA HIGH SPEED, EXTREMELY LOW NOISE CMOS LDO REGULATOR AP2125

Typical Performance Characteristics (Continued)

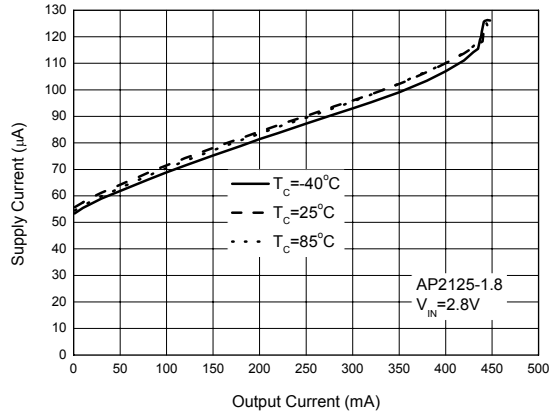


Figure 24. Supply Current vs. Output Current

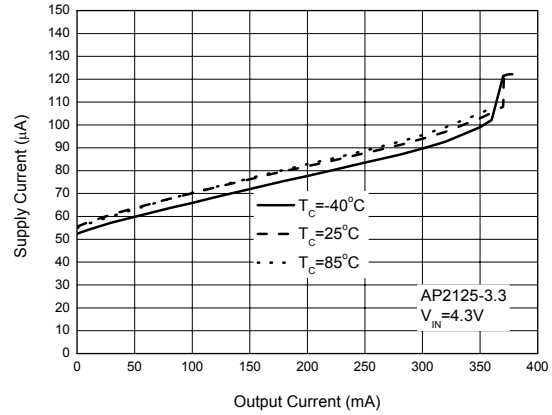


Figure 25. Supply Current vs. Output Current

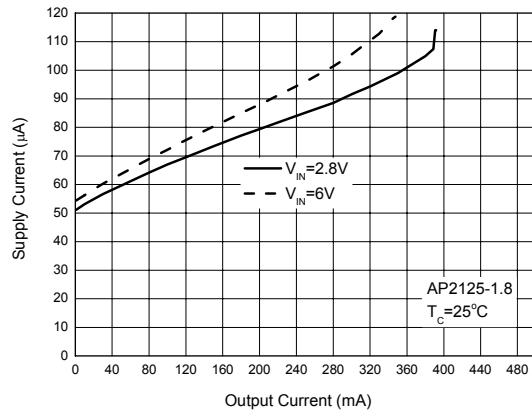


Figure 26. Supply Current vs. Output Current

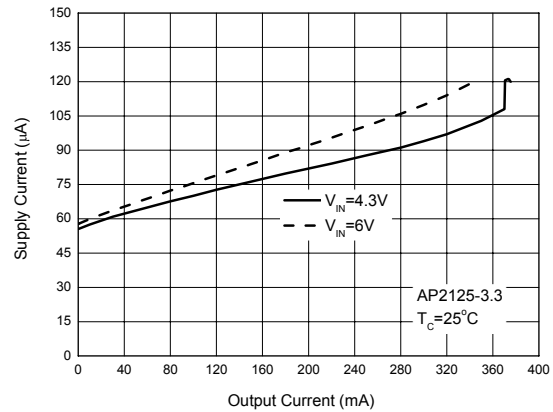


Figure 27. Supply Current vs. Output Current

Typical Performance Characteristics (Continued)

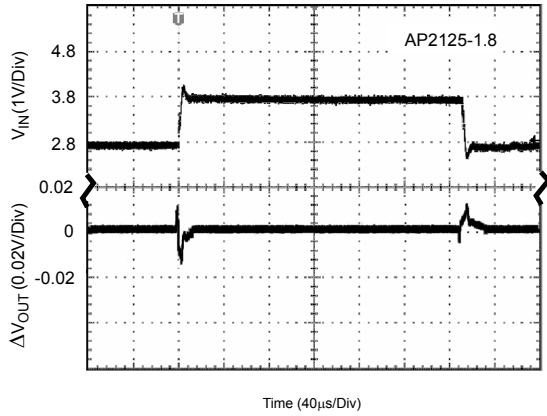


Figure 28. Line Transient
(Conditions: $I_{OUT}=30\text{mA}$, $C_{OUT}=1\mu\text{F}$, $V_{IN}=2.8$ to 3.8V)

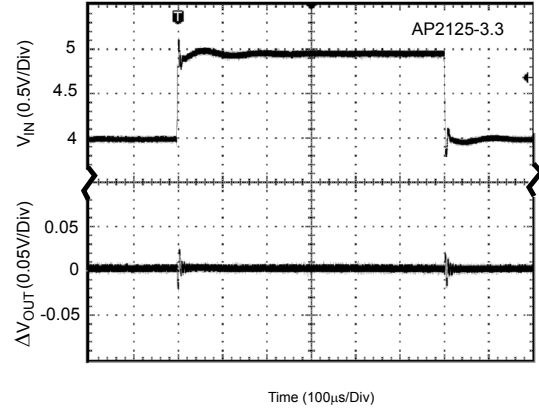


Figure 29. Line Transient
(Conditions: $I_{OUT}=30\text{mA}$, $C_{OUT}=1\mu\text{F}$, $V_{IN}=4$ to 5V)

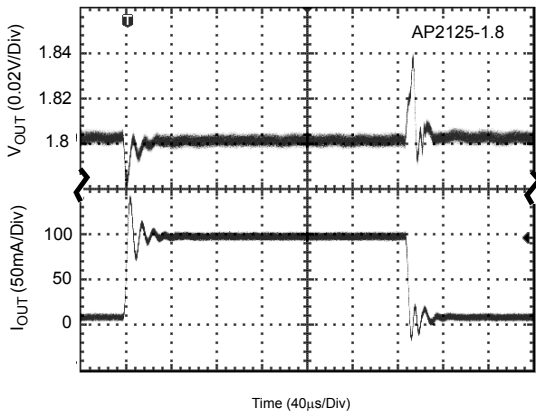


Figure 30. Load Transient
(Conditions: $I_{OUT}=10$ to 100mA , $C_{IN}=1\mu\text{F}$, $C_{OUT}=1\mu\text{F}$, $V_{IN}=2.8\text{V}$)

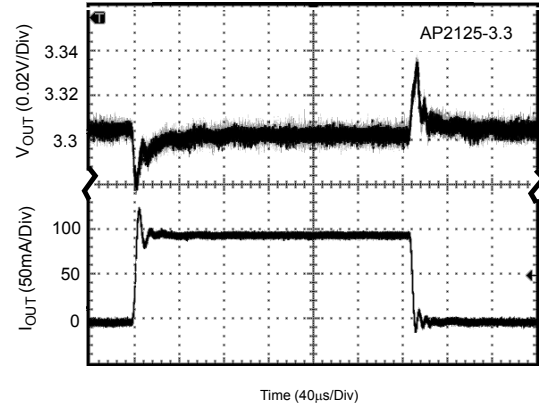


Figure 31. Load Transient
(Conditions: $I_{OUT}=10$ to 100mA , $C_{IN}=1\mu\text{F}$, $C_{OUT}=1\mu\text{F}$, $V_{IN}=4.3\text{V}$)

300mA HIGH SPEED, EXTREMELY LOW NOISE CMOS LDO REGULATOR AP2125

Typical Performance Characteristics (Continued)

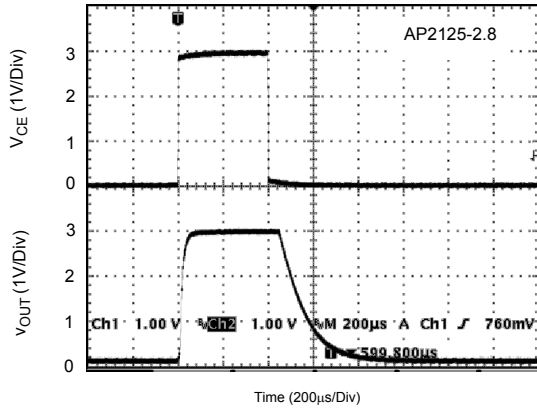


Figure 32. Enable Input Response and Auto-discharge
(Conditions: $V_{CE}=0$ to $3V$, $C_{IN}=1\mu F$,
 $C_{OUT}=1\mu F$, $V_{IN}=3V$, no load)

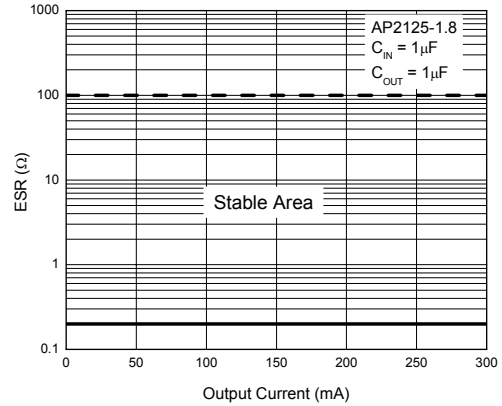


Figure 33. ESR vs. Output Current

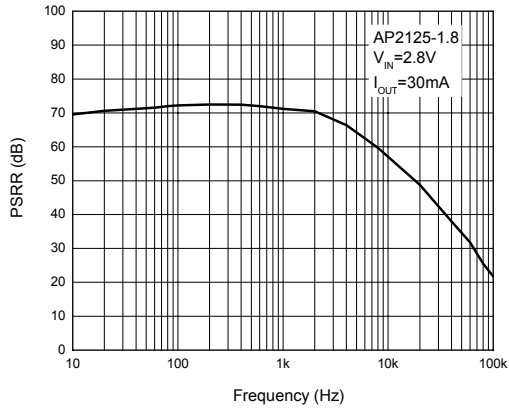


Figure 34. PSRR

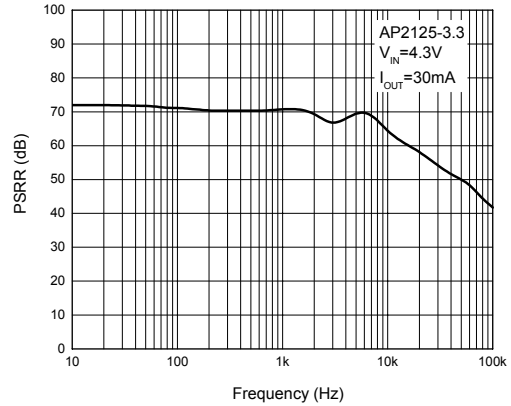


Figure 35. PSRR

300mA HIGH SPEED, EXTREMELY LOW NOISE CMOS LDO REGULATOR AP2125

Typical Performance Characteristics (Continued)

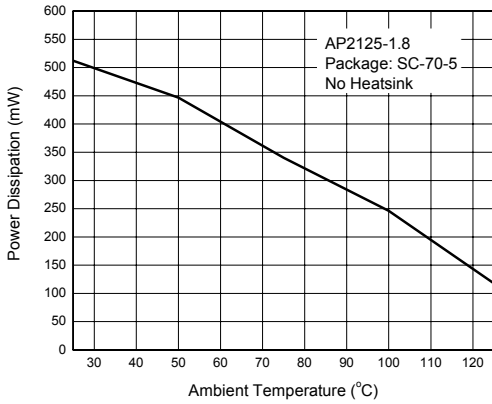


Figure 36. Power Dissipation vs. Ambient Temperature

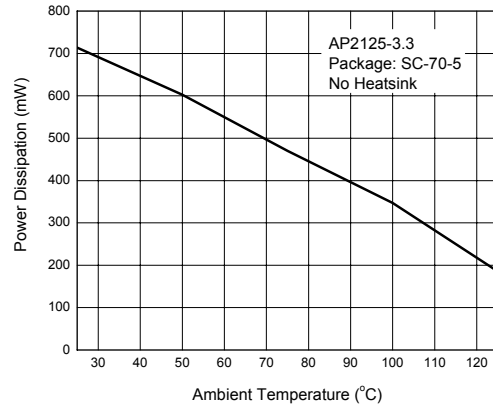


Figure 37. Power Dissipation vs. Ambient Temperature

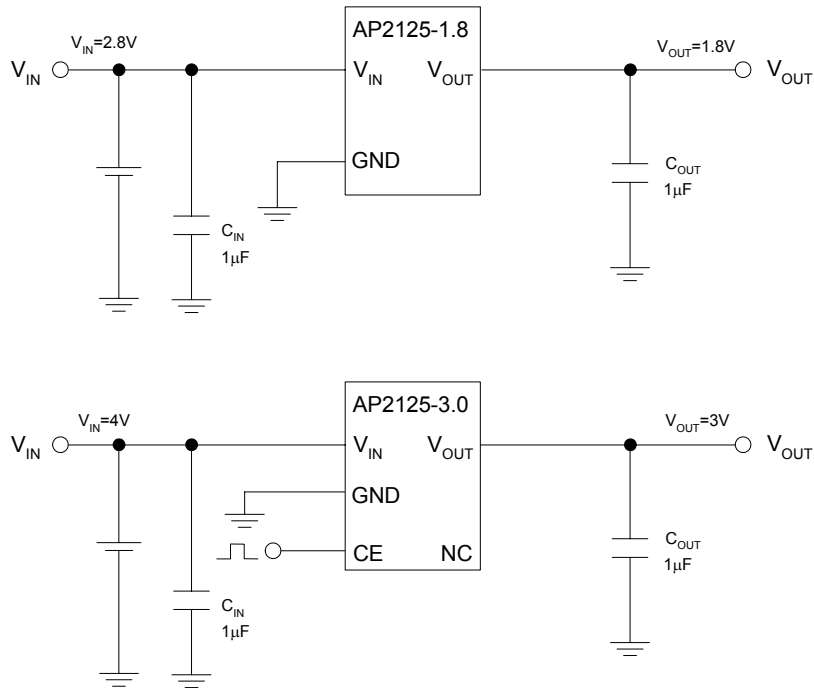
Typical Application


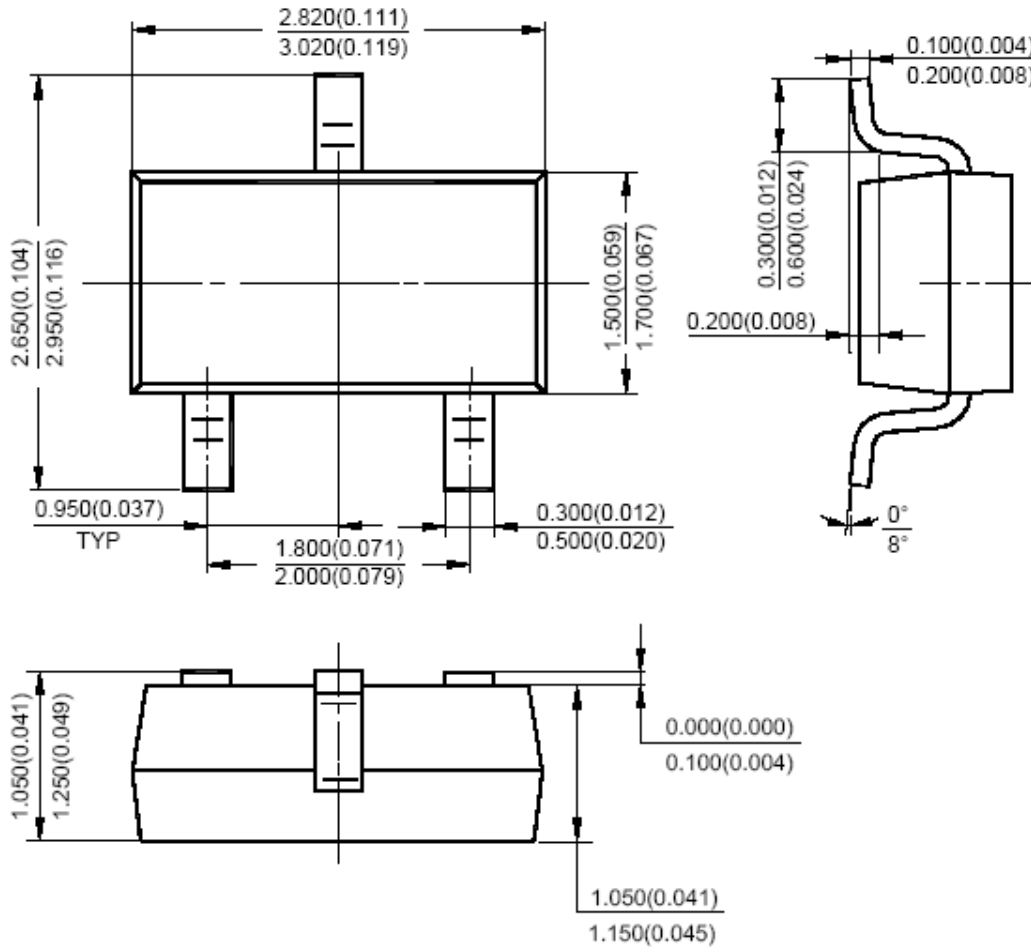
Figure 38. Typical Application of AP2125

300mA HIGH SPEED, EXTREMELY LOW NOISE CMOS LDO REGULATOR AP2125

Mechanical Dimensions

SOT-23-3

Unit: mm(inch)



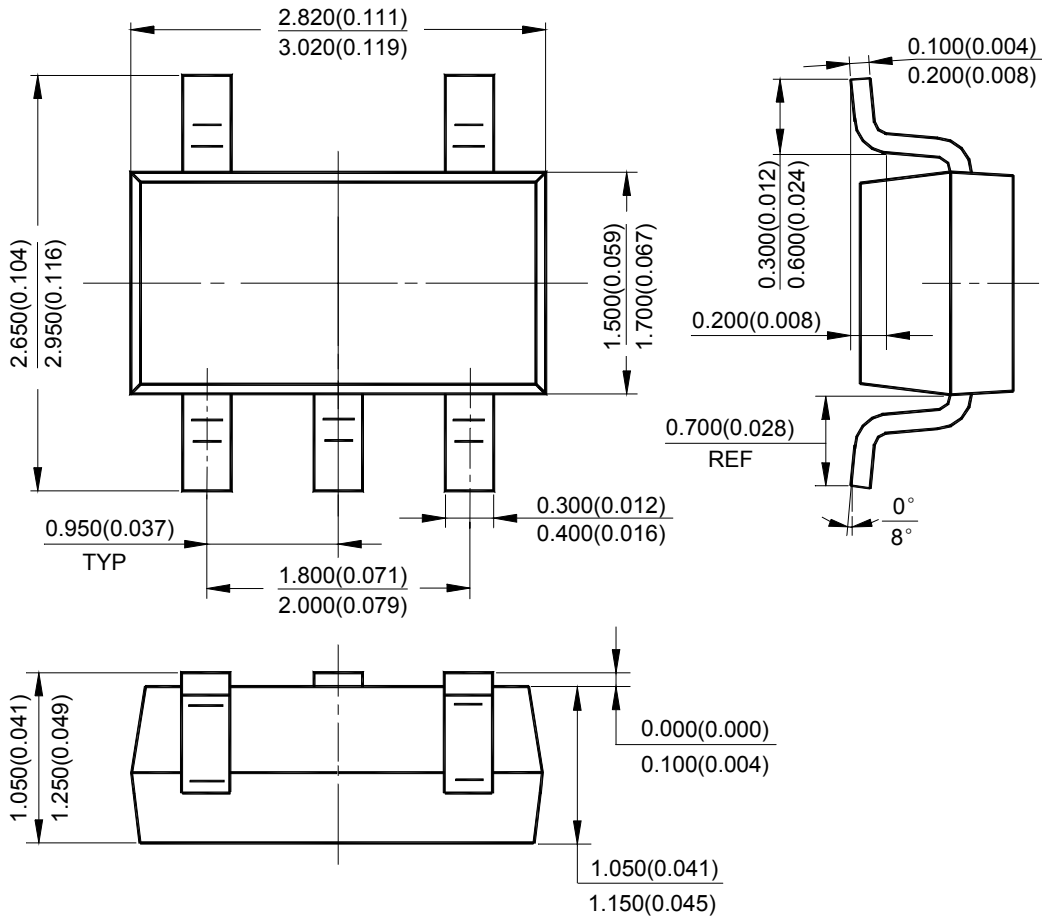


300mA HIGH SPEED, EXTREMELY LOW NOISE CMOS LDO REGULATOR AP2125

Mechanical Dimensions (Continued)

SOT-23-5

Unit: mm(inch)



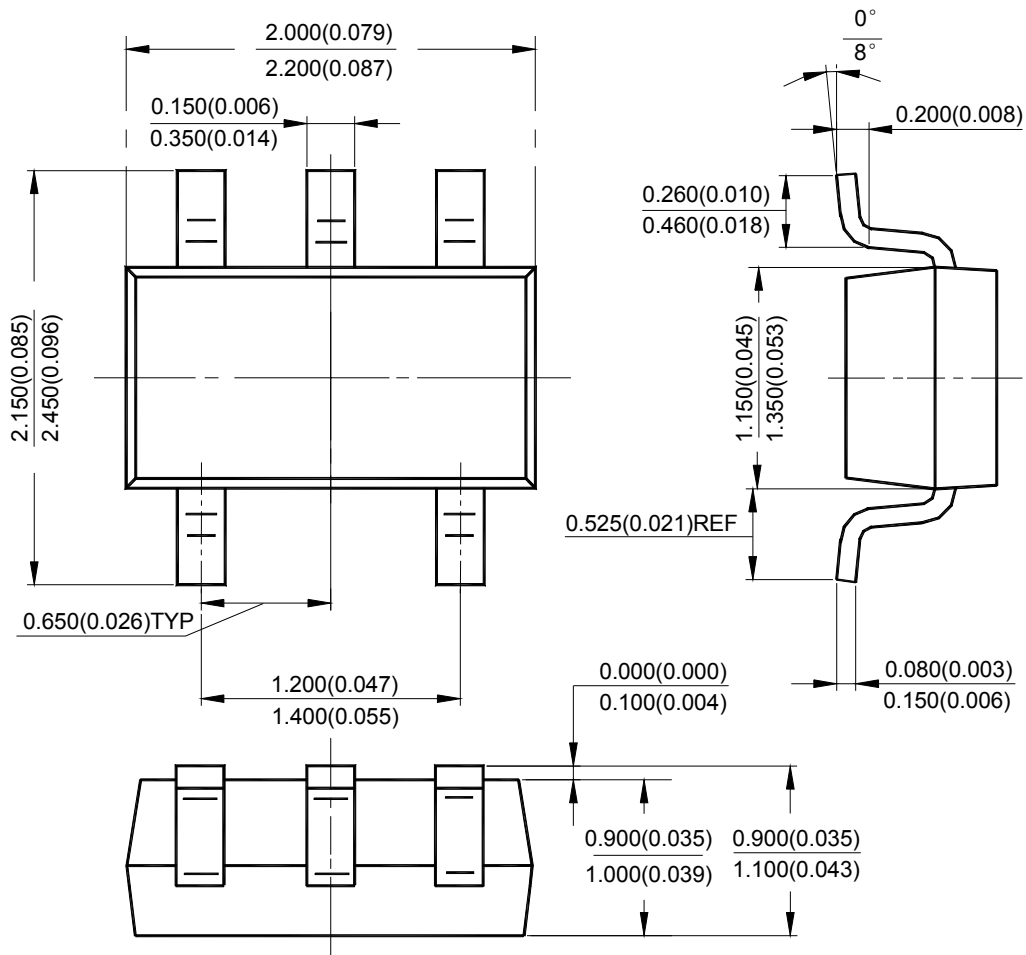


300mA HIGH SPEED, EXTREMELY LOW NOISE CMOS LDO REGULATOR AP2125

Mechanical Dimensions (Continued)

SC-70-5

Unit: mm(inch)



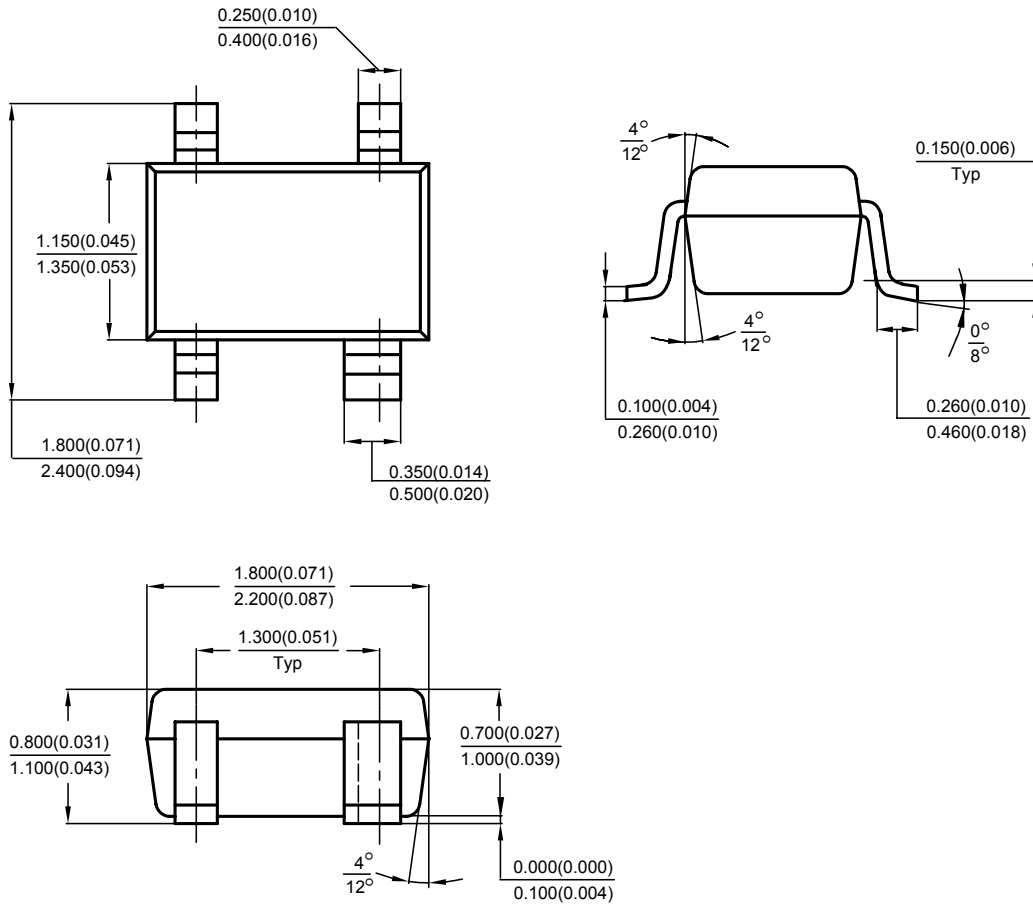


300mA HIGH SPEED, EXTREMELY LOW NOISE CMOS LDO REGULATOR AP2125

Mechanical Dimensions (Continued)

SC-82

Unit: mm(inch)





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